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Application Number	10/003,331
Filing Date	October 31, 2001
First Named Inventor	Slater
Group Art. Unit	
Examiner Name	
Attorney Docket Number	5000 113A

(use as many sheets as necessary)

Sheet	1	of	2
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Attorney Docket Number	5000.113A
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Struland

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¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the

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PTO/SB/08A (08-00)

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Sheet 2 of 2

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dv	12	SPIEL (aka "Spiess"), Aluminum implantation of p-SiC for ohmic contacts, First European Conference on Silicon Carbide and Related Materials (ECSCRM 96), Oct. 6-9, 1996, pp. 1414-1419, Vol. 6; no. 10, Elsevier, Switzerland	
	13	DEV ALOK ET AL, Low Contact Resistivity Ohmic Contacts to 6H-Silicon Carbide, Proceedings of the International Electron Devices Meeting, 1993, pp. 691-694, IEEE, New York	
	14	CHEN ET AL., Contact Resistivity of Re, Pt and Ta Films on n-Type Beta-SiC: Preliminary Results, Materials Science and Engineering, 01/01/1995, pp. 185-189, Vol. B29, no. 1/03, Elsevier Sequoia, Lausanne	
dv	15	PORTER ET AL, A critical review of ohmic and rectifying contacts for silicon carbide, Materials Science and Engineering, 11-01-1995, pp. 83-105, Vol. B34, no. 2/03, Elsevier Sequoia, Lausanne	

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